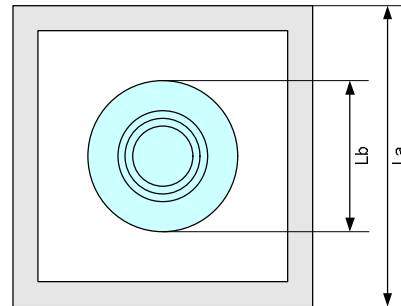


2SB030070MLJY SCHOTTKY BARRIER DIODE CHIPS
DESCRIPTION

- Ø 2SB030070MLJY is a schottky barrier diode chips fabricated in silicon epitaxial planar technology;
- Ø Low power losses, high efficiency;
- Ø Guard ring construction for transient protection;
- Ø High ESD capability;
- Ø High surge capability;
- Ø Packaged products are widely used in switching power suppliers, polarity protection circuits and other electronic circuits;
- Ø Chip Size:300 μ m X 300 μ m;
- Ø Chip Thickness: 155 \pm 20 μ m



Chip Topography and Dimensions

 La: Chip Size:300 μ m;

 Lb: Pad Size: 150 μ m;

ORDERING SPECIFICATIONS

Product Name	Specification
2SB030070MLJY	For Au and AlSi wire bonding package

ABSOLUTE MAXIMUM RATINGS

Parameters	Symbol	Ratings	Unit
Maximum Repetitive Peak Reverse Voltage	VRRM	70	V
Average Forward Rectified Current	IFAV	70	mA
Peak Forward Surge Current@8.3ms	IFSM	1	A
Maximum Operation Junction Temperature	TJ	125	$^{\circ}$ C
Storage Temperature Range	TSTG	-40~125	$^{\circ}$ C

ELECTRICAL CHARACTERISTICS (Tamb=25 $^{\circ}$ C)

Parameters	Symbol	Test Conditions	Min.	Max.	Unit
Reverse Voltage	VBR	IR=8 μ A	70	--	V
Forward Voltage	VF	IF=1.0mA	--	0.40	V
		IF=10mA	--	0.71	
		IF=15mA	--	0.95	
Reverse Current	IR	VR=50V	--	0.08	μ A
		VR=70V	--	8	